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### Vishay Semiconductors

## Insulated Gen 2 Schottky Rectifier Module, 300 A



SOT-227

#### **ADDITIONAL RESOURCES**



| PRIMARY CHARACTERISTICS                          |                                       |  |  |  |  |  |
|--|---------------------------------------|--|--|--|--|--|
| $I_{F(AV)}$ per module at $T_C = 132  ^{\circ}C$ | 300 A                                 |  |  |  |  |  |
| $V_{R}$  | 170 V                                 |  |  |  |  |  |
| $V_{FM}$ at 100 A, $T_C = 25$ °C                 | 0.79 V                                |  |  |  |  |  |
| Package  | SOT-227                               |  |  |  |  |  |
| Circuit configuration                            | Two separate diodes, parallel pin-out |  |  |  |  |  |

#### **FEATURES**

- Max. T<sub>J</sub> = 175 °C
- Two fully independent diodes
- Fully insulated package
- Trench MOS Barrier Schottky technology
- Ultra low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- · Industry standard outline
- Designed and qualified for industrial level

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- UL approved file E78996
- Material categorization: for definitions of compliance

#### **DESCRIPTION**

The VS-QA300FA17 insulated modules integrate two state of the art Trench MOS Schottky technology rectifiers in the compact, industry standard SOT-227 package.

These devices are thus intended for high frequency converters and switching power supplies.

| MAJOR RATINGS AND CHARACTERISTICS   |                         |             |    |  |  |
|-------------------------------------|-------------------------|-------------|----|--|--|
| SYMBOL CHARACTERISTICS VALUES UNITS |                         |             |    |  |  |
| V <sub>F</sub>                      | T <sub>J</sub> = 150 °C | 0.69        | V  |  |  |
| TJ                                  | Range                   | -55 to +175 | °C |  |  |

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C unless otherwise specified) |                                   |  |             |       |  |
|---|-----------------------------------|--|-------------|-------|--|
| PARAMETER   | SYMBOL                            | TEST CONDITIONS  | VALUES      | UNITS |  |
| Average forward current per module  | I <sub>F(AV)</sub>                | T <sub>C</sub> = 132 °C  | 300         | Α     |  |
| Cathode to anode voltage  | $V_R$                             |  | 170         | V     |  |
| Continuous forward current per diode  | I <sub>F</sub>                    | T <sub>C</sub> = 90 °C   | 330         | ^     |  |
| Single pulse forward current per diode  | I <sub>FSM</sub>                  | $T_C = 175$ °C, t = 6 ms, square   | 1575        | A     |  |
| Maximum power dissipation per diode   | $P_D$                             | T <sub>C</sub> = 90 °C   | 327         | W     |  |
| Non-repetitive avalanche energy per diode   | E <sub>AS</sub>                   | $T_J = 25  ^{\circ}\text{C},  I_{AS} = 27  \text{A},  L = 10  \text{mH}$ | 3700        | mJ    |  |
| RMS isolation voltage   | V <sub>ISOL</sub>                 | Any terminal to case, t = 1 min  | 2500        | V     |  |
| Operating junction and storage temperatures   | T <sub>J</sub> , T <sub>Stg</sub> |  | -55 to +175 | °C    |  |



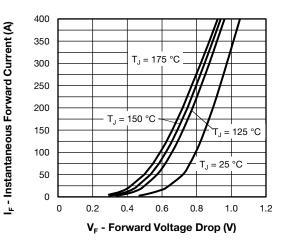
| <b>ELECTRICAL SPECIFICATIONS PER DIODE</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |   |   |      |      |      |       |
|--|---|---|------|------|------|-------|
| PARAMETER  | SYMBOL  | YMBOL TEST CONDITIONS                           |      | TYP. | MAX. | UNITS |
| Cathode to anode breakdown voltage   | $V_{BR}$  | I <sub>R</sub> = 2 mA                           | 170  | -    | -    |       |
|  | V   | I <sub>F</sub> = 100 A                          | -    | 0.79 | 0.85 |       |
| Forward voltage V <sub>FM</sub>  |   | I <sub>F</sub> = 100 A, T <sub>J</sub> = 150 °C | =    | 0.62 | =    | V     |
|  | I <sub>F</sub> = 200 A                          | -   | 0.89 | 0.98 |      |       |
|  |   | I <sub>F</sub> = 200 A, T <sub>J</sub> = 150 °C | =    | 0.75 | =    |       |
| Reverse leakage current I <sub>RM</sub>  | V <sub>R</sub> = 170 V                          | =   | 13   | 200  | μΑ   |       |
|  | T <sub>J</sub> = 125 °C, V <sub>R</sub> = 170 V | -   | 20   | -    | mA   |       |
| Junction capacitance   | C <sub>T</sub>                                  | V <sub>R</sub> = 170 V                          | -    | 737  | -    | pF    |

| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                         |  |                       |      |      |      |       |
|---|-------------------------|--|-----------------------|------|------|------|-------|
| PARAMETER   | SYMBOL                  | TEST CONDITIONS  |                       | MIN. | TYP. | MAX. | UNITS |
| Deverse receiver time   |                         | T <sub>J</sub> = 25 °C   | I <sub>F</sub> = 50 A | -    | 71   | -    | ns    |
| Reverse recovery time   | t <sub>rr</sub>         | T <sub>J</sub> = 125 °C  |                       | =    | 82   | -    |       |
| Peak recovery current I <sub>RRM</sub>  |                         | T <sub>J</sub> = 25 °C   |                       | -    | 7.1  | -    | Δ.    |
|   | T <sub>J</sub> = 125 °C | $di_F/dt = 200 \text{ A/}\mu\text{s}$<br>$V_R = 100 \text{ V}$ | =                     | 8.8  | -    | Α    |       |
| Reverse recovery charge   | Q <sub>rr</sub>         | T <sub>J</sub> = 25 °C   | -n                    | -    | 252  | -    | ~C    |
|   |                         | T <sub>J</sub> = 125 °C  |                       | -    | 352  | -    | nC    |

| THERMAL - MECHANICAL SPECIFICATIONS     |                   |                       |      |      |            |             |
|---|-------------------|-----------------------|------|------|------------|-------------|
| PARAMETER                               | SYMBOL            | TEST CONDITIONS       | MIN. | TYP. | MAX.       | UNITS       |
| Junction-to-case, single leg conducting |                   |                       | -    | -    | 0.26       |             |
| Junction-to-case, both leg conducting   | $R_{thJC}$        |                       | -    | -    | 0.13       | °C/W        |
| Case-to-heatsink                        | R <sub>thCS</sub> | Flat, greased surface | -    | 0.1  | -          |             |
| Weight                                  |                   |                       | -    | 30   | -          | g           |
| Mounting torque                         |                   | Torque to terminal    | -    | -    | 1.1 (9.7)  | Nm (lbf.in) |
| Mounting torque                         |                   | Torque to heatsink    | -    | -    | 1.8 (15.9) | Nm (lbf.in) |
| Case style                              |                   |                       |      | SC   | T-227      |             |

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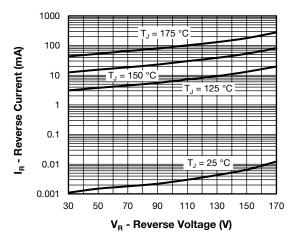


Fig. 1 - Typical Forward Voltage Drop vs. Instantaneous Forward Current (Per Diode)

Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

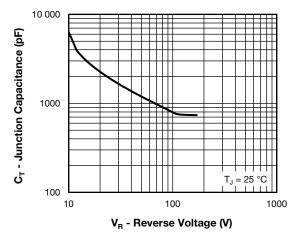


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Diode)

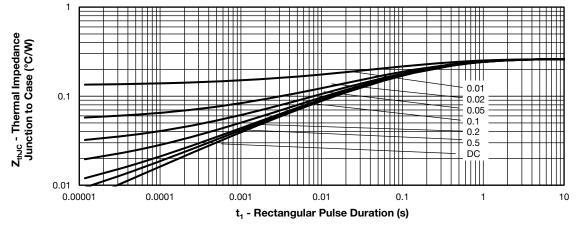


Fig. 4 - Maximum Thermal Impedance Junction-to-Case Characteristics (Per Diode)

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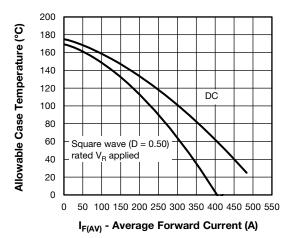


Fig. 5 - Maximum Current Rating Capability (Per Diode)

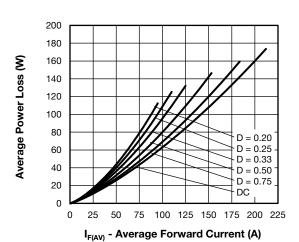


Fig. 6 - Forward Power Loss Characteristics (Per Diode)

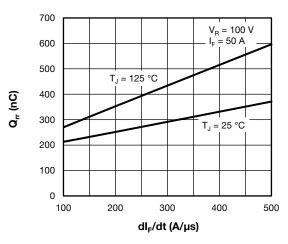


Fig. 7 - Typical Reverse Recovery Charge vs dl<sub>E</sub>/dt (Per Diode)

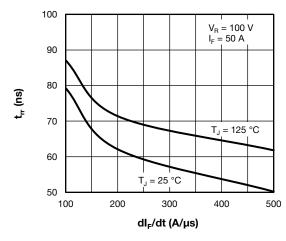


Fig. 8 - Typical Reverse Recovery Time vs dl<sub>F</sub>/dt (Per Diode)

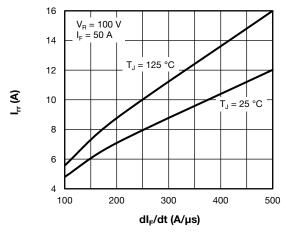


Fig. 9 - Typical Reverse Recovery Current vs dIFdt (Per Diode)

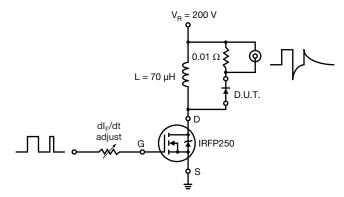
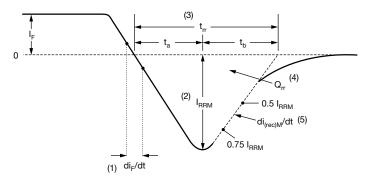


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

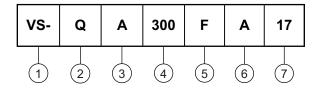
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 11 - Reverse Recovery Waveform and Definitions



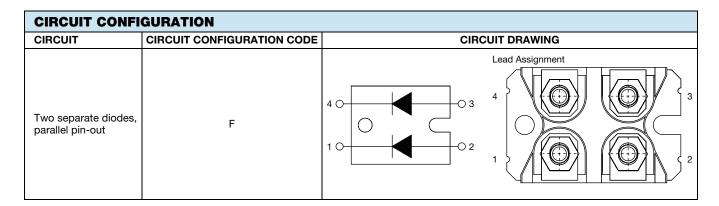
### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Vishay Semiconductors product
- 2 Schottky technologies
- Present silicon generation
- Current rating (300 = 300 A)
- 5 Circuit configuration (two separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (17 = 170 V)

Quantity per tube is 10, M4 screw and washer included



| LINKS TO RELATED DOCUMENTS                 |                          |  |  |  |  |
|--|--------------------------|--|--|--|--|
| Dimensions <u>www.vishay.com/doc?95423</u> |                          |  |  |  |  |
| Part marking information                   | www.vishay.com/doc?95425 |  |  |  |  |

### SOT-227 Generation 2

### **DIMENSIONS** in millimeters (inches)





#### Note

· Controlling dimension: millimeter



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